

L Number	Hits	Search Text	DB	Time stamp
-	60	single near3 chamber and laser near4 anneal\$4 and (TFT or thin adj film adj transistor)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/02/02 16:37
-	10	single near3 chamber same laser near4 anneal\$4 same deposit\$4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/02/02 16:39
-	100	chamber same laser near4 anneal\$4 same deposit\$4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/02/02 16:56
-	2	6258173.pn.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/02/02 16:42
-	57	(chamber same laser near4 anneal\$4 same deposit\$4) and (TFT or thin adj film adj transistor)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/02/02 16:59
-	99	single near4 chamber same anneal\$4 same deposit\$4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/02/02 17:03
-	13	(single near4 chamber same anneal\$4 same deposit\$4) and (TFT or thin adj film adj transistor)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/02/02 17:01
-	14	(single near4 chamber same anneal\$4 same deposit\$4) and laser near3 anneal\$4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/02/02 17:02
-	36	single near4 chamber same (laser or enerergy adj beam) same deposit\$4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/02/02 17:10
-	43	chamber same (laser or eneregy adj beam) same deposit\$4 same in\$lsitu	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/02/02 17:14